

1MBI75U4F-120L-50

IGBT Modules

IGBT MODULE (U series) 1200V / 75A / 1 in one package

Features

High speed switching Voltage drive Low Inductance module structure

■ Applications

Inverter DB for Motor Drive AC and DC Servo Drive Amplifier (DB) Active PFC Industrial machines



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

| Items | s | | Conditions | | Maximum ratings | | |
|-----------------------------|---------------------------------------|------------------|------------|---------|-----------------|------|--|
| Collector-Emitter voltage | | Vces | | | 1200 | V | |
| Gate-Emitter voltage | | V _{GES} | | | ±20 | | |
| Collector current | | Ic | Continuous | Tc=25°C | 100 | | |
| | | | Continuous | Tc=80°C | 75 | | |
| | | Icp | 1 ma | Tc=25°C | 200 | ٨ | |
| | | | 1ms | Tc=80°C | 150 | Α | |
| | | -lc | | | 35 | | |
| | | -lc pulse | 1ms | | 70 | | |
| Collector power dissipation | | Pc | 1 device | | 400 | W | |
| Reverse voltage for FWD | | VR | | | 1200 | V | |
| Forword current for FWD | | IF | Continuous | | 100 | Α | |
| | | IF pulse | 1ms | | 200 | | |
| Junction temperature | | Tj | | | +150 | °C | |
| Storage temperature | | Tstg | | | -40~+125 | °C | |
| Isolation voltage | Between terminal and copper base (*1) | V _{iso} | AC : 1min. | | 2500 | VAC | |
| Screw torque | Mounting (*2) | | 0.5 | | 2.5 | Nime | |
| | Terminals (*3) | 1- | | | 3.5 | Nm | |

Note *1: All terminals should be connected together when isolation test will be done.

Note *2: Recommendable Value : 2.5 to 3.5 Nm (M5 or M6) Note *3: Recommendable Value : 2.5 to 3.5 Nm (M5)

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● Electrical characteristics (at Tj= 25°C unless otherwise specified)

| Items | Cumbala | Conditions | Conditions | | Characteristics | | |
|--|--|--|---|------|-----------------|------|-------|
| nems | Symbols | Symbols Conditions | | min. | typ. | max. | Units |
| Zero gate voltage collector current | Ices | V _{GE} = 0V, V _{CE} = 120 | V _{GE} = 0V, V _{CE} = 1200V | | - | 1.0 | mA |
| Gate-Emitter leakage current | nitter leakage current IGES VCE = 0V, VGE = ±20V | | V | - | - | 200 | nA |
| Gate-Emitter threshold voltage | V _{GE (th)} | V _{CE} = 20V, I _C = 75mA | | 4.5 | 6.5 | 8.5 | V |
| | V _{CE} (sat) | | Tj=25°C | - | 2.05 | 2.20 | V |
| Callantan Fruittan anti-matian waltana | (terminal) | V _{GE} = 15V | Tj=125°C | - | 2.25 | - | |
| Collector-Emitter saturation voltage | V _{CE} (sat) | Ic = 75A | Tj=25°C | - | 1.90 | 2.05 | |
| | (chip) | | Tj=125°C | - | 2.10 | - | |
| Input capacitance | Cies | V _{GE} = 0V, V _{CE} = 10V | V _{GE} = 0V, V _{CE} = 10V, f = 1MHz | | 8 | - | nF |
| | ton | | | - | 0.32 | 1.20 | |
| Turn-on time | tr | | Vcc = 600V, Ic = 75A Vce = ±15V. Rc = 9.1Ω | | | 0.60 | μs |
| | tr(i) | | | | | - | |
| - cc. | toff | V GE = ±15V, RG = 9. | VGE = 113V, RG = 9.112 | | 0.41 | 1.00 | |
| Turn-off time | tf | | | | 0.07 | 0.30 | |
| | V _F | | Tj=25°C | - | 1.65 | 2.00 | V |
| P | (terminal) | $V_{GE} = 0V$ | Tj=125°C | - | 1.75 | - | |
| Forward on voltage | VF | I _F = 35A | Tj=25°C | - | 1.60 | 1.85 | |
| | (chip) | | Tj=125°C | - | 1.70 | - | |
| Reverse Current | IR | V _{CE} = 1200V | V _{CE} = 1200V | | - | 1.0 | mA |
| | VF | | Tj=25°C | - | 1.75 | 1.90 | V |
| P | (terminal) | $V_{GE} = 0V$ | Tj=125°C | - | 1.90 | - | |
| Forward on voltage | VF | I _F = 100A | Tj=25°C | - | 1.60 | 1.75 | |
| | (chip) | | Tj=125°C | - | 1.75 | - | |
| Reverse recovery time | trr | I _F = 100A | | - | - | 0.35 | μs |
| Lead resistance, terminal-chip(*4) | R lead | | | - | 1.39 | - | mΩ |

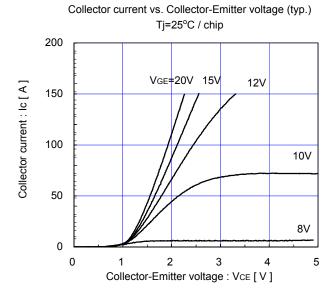
Note *4: Biggest internal terminal resistance among arm.

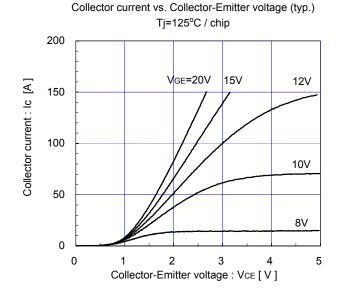
● Thermal resistance characteristics

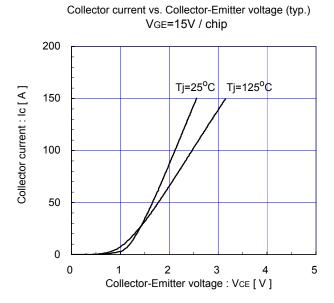
| Items | Symbolo | Conditions | Characteristics | | | Units | |
|------------------------------|----------|----------------------------|-----------------|------|------|-------|--|
| items | Symbols | Conditions | min. | typ. | max. | Units | |
| | | IGBT | - | - | 0.31 | | |
| Thermal resistance (1device) | Rth(j-c) | Inverse Diode | - | - | 0.88 | °C/W | |
| | | FWD | - | - | 0.40 | | |
| Contact thermal resistance | Rth(c-f) | with Thermal Compound (*5) | | 0.05 | - | | |

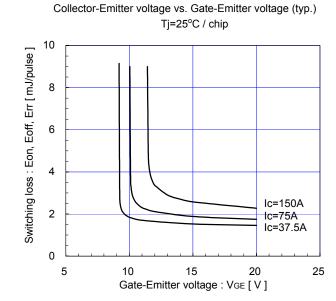
Note $^{\star}5$: This is the value which is defined mounting on the additional cooling fin with thermal compound.

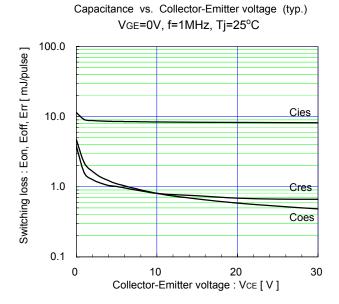
■ Characteristics (Representative)

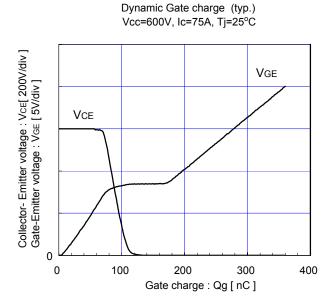


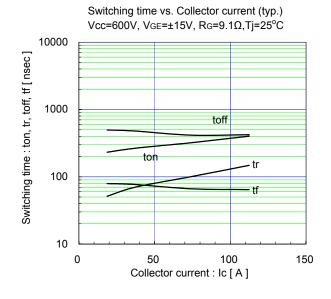


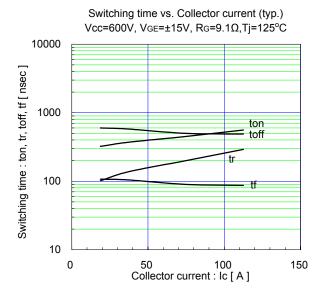


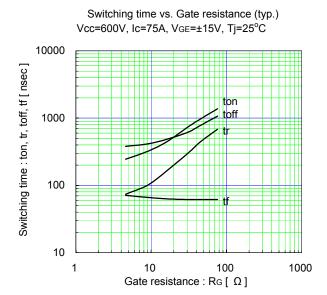


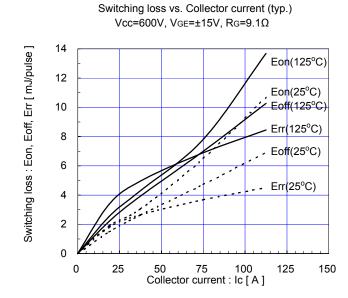


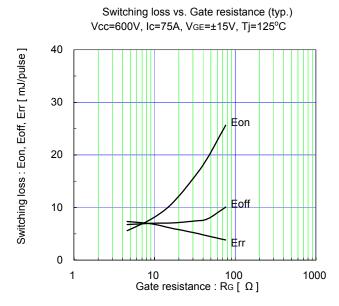


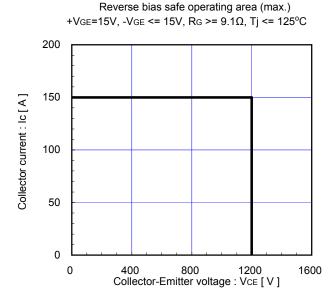


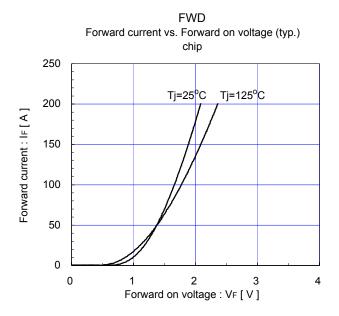


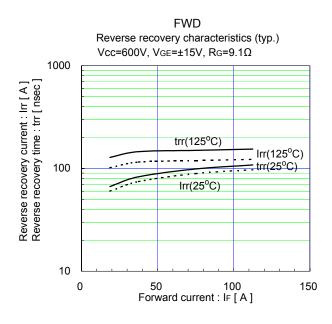


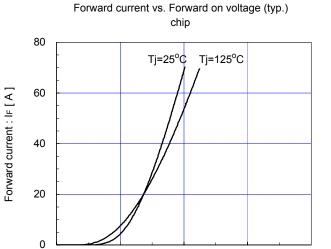










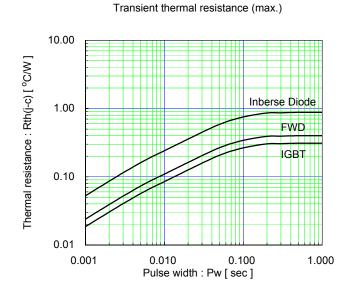


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Forward on voltage : VF [V]

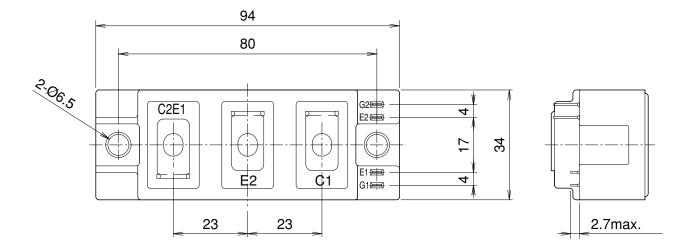
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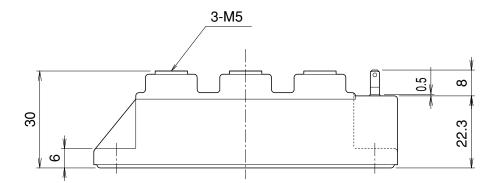
Inverse Diode



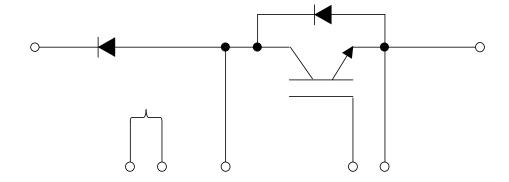
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Outline Drawings, mm





■ Equivalent Circuit Schematic



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Trunk communications equipment

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